# DRA9113Z (Tentative)

### Silicon PNP epitaxial planar type

#### For digital circuits

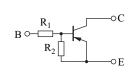
#### Absolute Maximum Ratings $T_a = 25^{\circ}C$

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	-50	V	
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	-50	V	
Collector current	I <sub>C</sub>	I <sub>C</sub> -100		
Total power dissipation	P <sub>T</sub>	125	mW	
Junction temperature	Tj	150	°C	
Storage temperature	T <sub>stg</sub>	-55 to +150	°C	

- Package
- Code
- SSMini3-F3-B
- Pin Name
  - 1: Base
  - 2: Emitter
  - 3: Collector

Marking Symbol: L1

Internal Connection



Resistance	R <sub>1</sub>	1	kΩ
value	R <sub>2</sub>	10	kΩ

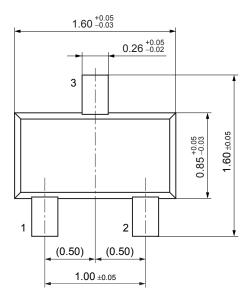
#### Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

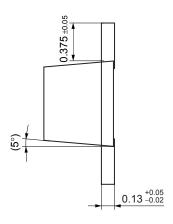
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	$I_{\rm C} = -10 \ \mu {\rm A}, I_{\rm E} = 0$	-50			V
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_{\rm C} = -2  {\rm mA},  I_{\rm B} = 0$	-50			V
Collector-base cutoff current (Emitter open)	I <sub>CBO</sub>	$V_{CB} = -50 \text{ V}, I_E = 0$			- 0.1	μΑ
Collector-emitter cutoff current (Base open)	I <sub>CEO</sub>	$V_{\rm CE} = -50$ V, $I_{\rm B} = 0$			- 0.5	μΑ
Emitter-base cutoff current (Collector open)	I <sub>EBO</sub>	$V_{\rm EB} = -6$ V, $I_{\rm C} = 0$			-1.5	mA
Forward current transfer ratio	$\mathbf{h}_{\mathrm{FE}}$	$V_{\rm CE} = -10$ V, $I_{\rm C} = -5$ mA	30			_
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_{\rm C} = -10 \text{ mA}, I_{\rm B} = -0.5 \text{ mA}$			-0.25	V
Output voltage high-level	V <sub>OH</sub>	$V_{CC} = -5 V, V_B = -0.5 V, R_L = 1 k\Omega$	-4.9			V
Output voltage low-level	V <sub>OL</sub>	$V_{\rm CC} = -5 \text{ V}, V_{\rm B} = -2.5 \text{ V}, R_{\rm L} = 1 \text{ k}\Omega$			- 0.2	V
Input resistance	R <sub>1</sub>		-30%	1	+30%	kΩ
Resistance ratio	$R_1 / R_2$		0.08	0.10	0.12	

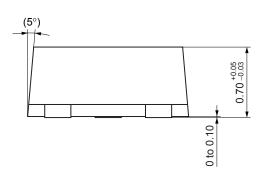
Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

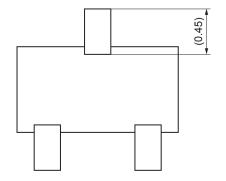
### SSMini3-F3-B

Unit: mm









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